

**SURFACE MOUNT GLASS PASSIVATED
HIGH EFFICIENCY SILICON RECTIFIER**
VOLTAGE RANGE 50 to 1000 Volts CURRENT 1.0 Ampere

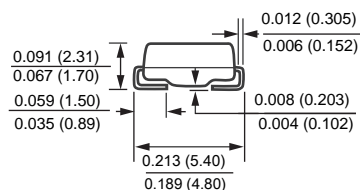
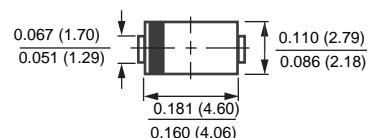
FEATURES

- * Glass passivated device
- * Ideal for surface mounted applications
- * Low leakage current
- * Metallurgically bonded construction
- * Mounting position: Any
- * Weight: 0.066 gram
- * RoHS product for packing code suffix "G"
- Halogen free product for packing code suffix "H"

MECHANICAL DATA

- * Epoxy: Device has UL flammability classification 94V-O

SMA/DO-214AC



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

MAXIMUM RATINGS (@ TA=25 °C unless otherwise noted)

RATINGS	SYMBOL	HFM101	HFM102	HFM103	HFM104	HFM105	HFM106	HFM107	HFM108	UNITS
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	300	400	600	800	1000	Volts
Maximum RMS Voltage	V_{RMS}	35	70	140	210	280	420	490	700	Volts
Maximum DC Blocking Voltage	V_{DC}	50	100	200	300	400	600	800	1000	Volts
Maximum Average Forward Rectified Current at $T_A = 50^\circ\text{C}$	I_O	1.0								Amps
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	30								Amps
Typical Thermal Resistance (Note 1)	$R_{\theta JL}$	27								$^\circ\text{C/W}$
Typical Thermal Resistance (Note 1)	$R_{\theta JA}$	75								$^\circ\text{C/W}$
Typical Junction Capacitance (Note 2)	C_J	15				12				pF
Operating Temperature Range	T_J	-65 to + 175								$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-65 to + 175								$^\circ\text{C}$

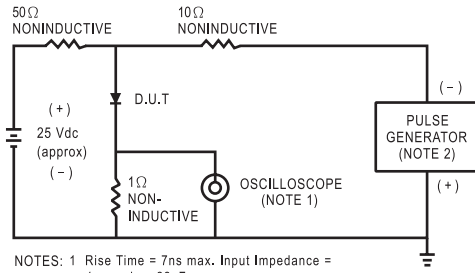
ELECTRICAL CHARACTERISTICS (@TA=25 °C unless otherwise noted)

CHARACTERISTICS	SYMBOL	HFM101	HFM102	HFM103	HFM104	HFM105	HFM106	HFM107	HFM108	UNITS	
Maximum Instantaneous Forward Voltage at 1.0A DC	V_F	1.0			1.3		1.7			Volts	
Maximum Full Load Reverse Current, Full cycle Average $T_A = 55^\circ\text{C}$	I_R	50								μA	
Maximum Average Reverse Current @ $T_A = 25^\circ\text{C}$		5								μA	
at Rated DC Blocking Voltage @ $T_A = 125^\circ\text{C}$		100								μA	
Maximum Reverse Recovery Time (Note 4)	t_{rr}	50					75				nSec

- NOTES : 1. Thermal Resistance : Mounted on PCB.
2. Measured at 1 MHz and applied reverse voltage of 4.0 volts.
3. Test Conditions: $I_F = 0.5\text{A}$, $I_R = -1.0\text{A}$, $I_{RR} = -0.25\text{A}$.

RATING AND CHARACTERISTIC CURVES (HFM101 THRU HFM108)

FIG. 1 - TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1 Rise Time = 7ns max. Input Impedance = 1 megohm, 22pF.
2. Rise Time = 10ns max. Source Impedance = 50 ohms.

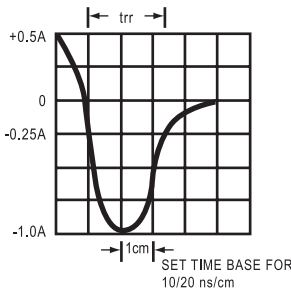


FIG. 2 - TYPICAL FORWARD CURRENT DERATING CURVE

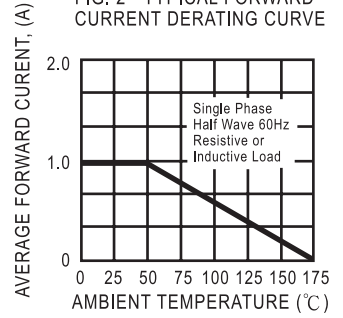


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

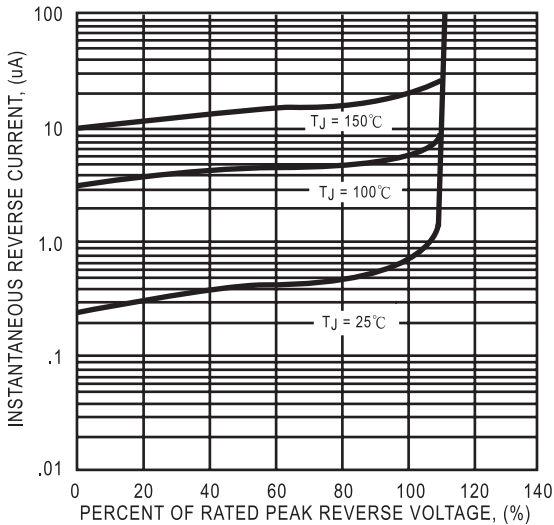


FIG. 4 - TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

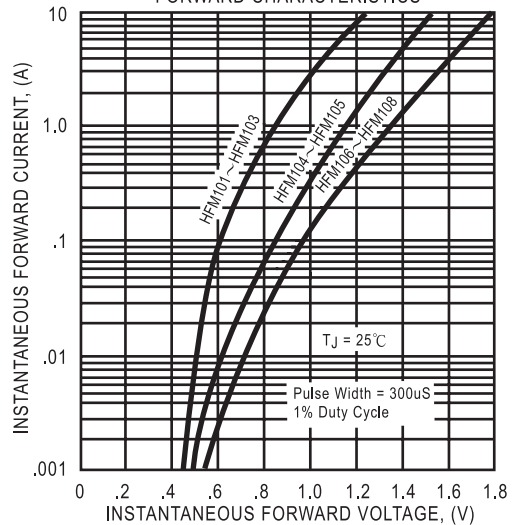


FIG. 5 - MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

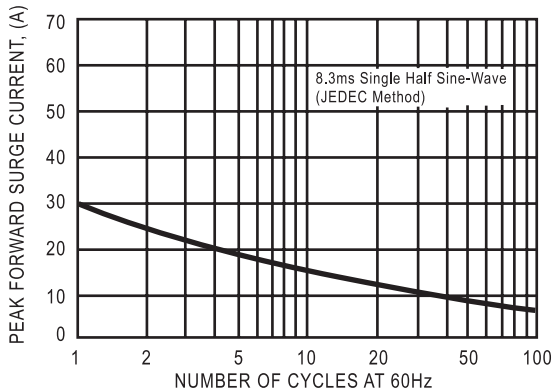


FIG. 6 - TYPICAL JUNCTION CAPACITANCE

